

# **DESCRIPTION**

The BSS84W is available in SOT-323 packages.

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BVDSS	RDSON	ID
-60V	4Ω	-0.18A

#### **FEATURE**

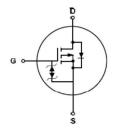
- Low On -Resistance
- Low Gate threshold voltage
- Low input Capacitance
- Reliable and Rugged
- **ESD Protected**

#### **APPLICATION**

- General purpose interfacing switch
- Analog load switch
- Power management functions

# **PIN DESCRIPTION**





SOT-323

### ORDERING INFORMATION

Package Type	Part Number	
SOT-323	BSS84W	
SPQ	3,000pcs/Reel	
AiT provides all RoHS products		

Pin#	Symbol	Function
1	G	Gate
2	S	Source
3	D	Drain

#### **ABSOLUTE MAXIMUM RATINGS**

T<sub>A</sub> = 25°C, unless otherwise specified.

V <sub>DSS</sub> , Drain-Source Voltage	-60 V
V <sub>GSS</sub> , Gate-Source Voltage	±20 V
I <sub>D</sub> , Continue Drain Current	-0.18 A
I <sub>DM</sub> <sup>(1)</sup> , Pulsed Drain Current	-0.45 A
Is, Diode Continuous Forward Current	-0.1 A
T <sub>J</sub> , Maximum Junction Temperature	150 °C
T <sub>STG</sub> , Storage Temperature Range	50 ~ 150 °C
R <sub>BJA</sub> <sup>(2)</sup> , Thermal Resistance-Junction to Ambient	400 °C/W

<sup>(1)</sup> Current limit by max. junction temperature.

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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<sup>(2)</sup> The ReJA is the sum of the thermal impedance from junction to ambient and depend on package type.

# **ELECTRICAL CHARACTERISTICS**

 $T_C$  = 25°C, unless otherwise specified.

Parameter	Symbol	Condition	Min	Тур.	Max	Unit
Static Characteristics (3)						
Drain-Source Breakdown Voltage	Bvdss	V <sub>GS</sub> = 0 V, I <sub>DS</sub> = -250 μA	-60	-	-	V
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> = -48 V, V <sub>GS</sub> = 0 V	-	-	1	μΑ
		T <sub>J</sub> = 85 °C	-	-	30	
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{DS} = V_{GS},$ $I_{D} = -250 \mu A$	-1.1	-1.8	-2.5	٧
Gate Leakage Current	lgss	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V	-	-	±10	μΑ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	$V_{GS} = -10V$ , $I_{DS} = -100 \text{ mA}$	-	4.0	6.0	- Ω
Diam-Source On-State Resistance		$V_{GS} = -4.5V$ , $I_{DS} = -100 \text{ mA}$	-	4.5	7.0	
Drain Forward Voltage	V <sub>SD</sub>	$V_{GS} = 0V$ , $I_{SD} = -100 \text{ mA}$	-	-0.85	-1.1	٧

<sup>(3)</sup> MOS static characteristics test by wafer level (CP).

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### TYPICAL PERFORMANCE CHARACTERISTICS

Fig 1. Output Characteristics

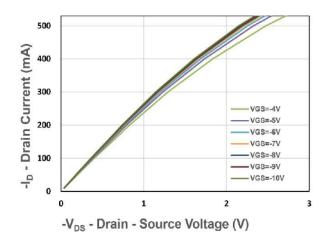


Fig 3. On-Resistance vs. VGS

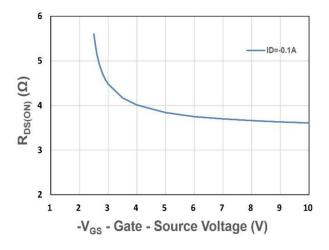


Fig 5. Drain-Source on Resistance

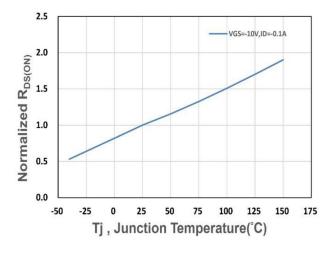


Fig 2. On-Resistance vs. ID

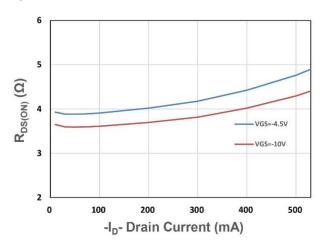


Fig 4. Gate Threshold Voltage

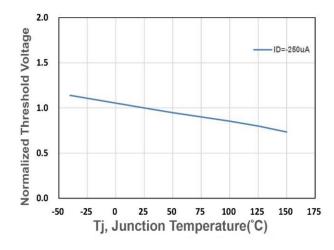
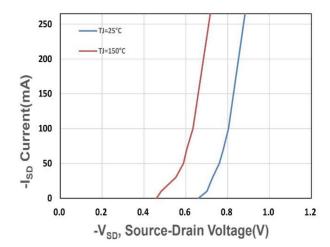


Fig 6. Source-Drain Diode Forward



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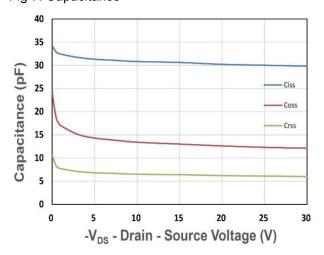


Fig 9. Power Dissipation

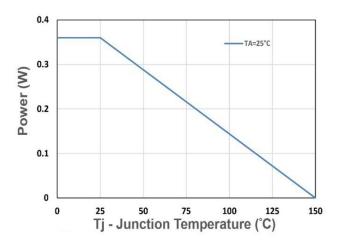


Fig 11. Sate Operating Area

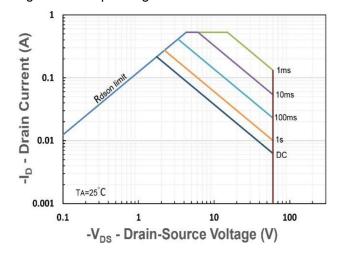


Fig 8. Gate Charge Characteristics

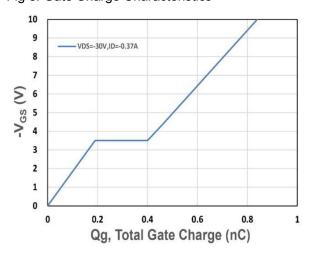


Fig 10. Drain Current

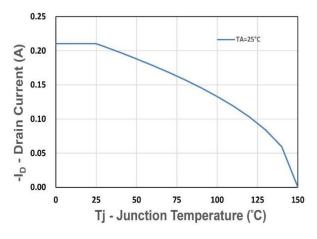
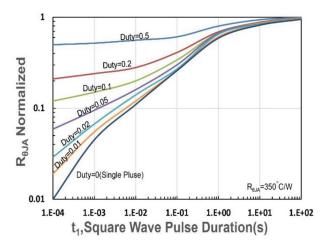


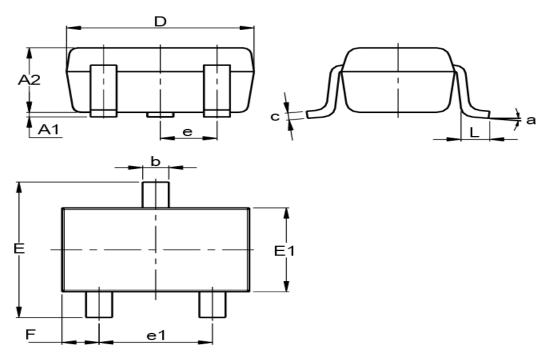
Fig 12. R<sub>0JA</sub> Transient Thermal Impedance



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# **PACKAGE INFORMATION**

Dimension in SOT-323 (Unit: mm)



Complete I	Millimeter		
Symbol	Min.	Max.	
A1	0.000	0.100	
A2	0.800	1.000	
b	0.200	0.400	
С	0.080	0.180	
D	1.000	2.220	
Е	2.000	2.450	
E1	1.150	1.350	
е	0.650 TYP.		
e1	1.200	1.400	
F	0.250	0.475	
L	0.250	0.460	
а	0°	8°	

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BSS84W MOSFET -60V, -0.18A P-CHANNEL ENHANCEMENT

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